

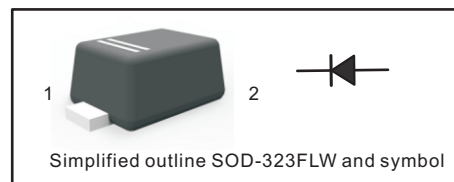


### FEATURES

- For surface mounted applications
- Glass Passivated Chip Junction
- Fast reverse recovery time
- Ideal for automated placement
- Lead free in comply with EU RoHS 2011/65/EU directives

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings at 25 °C

Parameter	Symbols	1N4148WF	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Maximum RMS voltage	$V_{RMS}$	75	V
Continuous Forward Current	$I_F$	150	mA
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	0.5 1 4	A
		at 1s	
		at 1ms	
		at 1us	
Total Power Dissipation	$P_{tot}$	300	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 ~ +150	°C

### Characteristics at $T_a = 25\text{ °C}$

Parameter	Symbols	1N4148WF	Units
Reverse Breakdown Voltage at $I_R = 1\mu\text{A}$	$V_{(BR)R}$	75	V
Maximum Forward Voltage	$V_F$	0.715 0.855 1.00 1.25	V
		at 1 mA	
		at 10 mA	
		at 50 mA	
		at 150 mA	
Peak Reverse Current	$I_R$	0.025 1 30 50	$\mu\text{A}$
		at $V_R = 20\text{V}$ $T_j = 25\text{°C}$	
		at $V_R = 75\text{V}$ $T_j = 25\text{°C}$	
		at $V_R = 25\text{V}$ $T_j = 150\text{°C}$	
		at $V_R = 75\text{V}$ $T_j = 150\text{°C}$	
Typical Junction Capacitance	$C_j$	2	pF
		f=1MHz, $V_R = 0\text{V}$	
Maximum Reverse Recovery Time <sup>(1)</sup>	$t_{rr}$	4	ns

(1) Measured with  $I_F = I_R = 10\text{mA}$ ,  $I_n = 0.1 * I_R$ ,  $R_L = 100\Omega$



Fig.1 Power Derating Curve

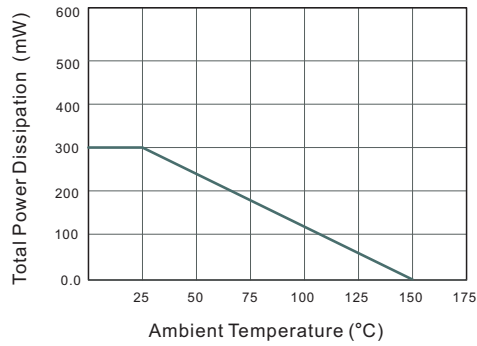


Fig.2 Typical Reverse Characteristics

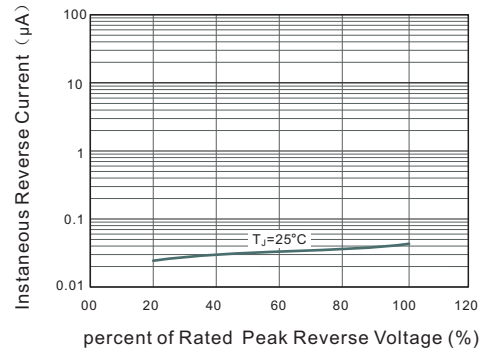


Fig.3 Typical Instantaneous Forward Characteristics

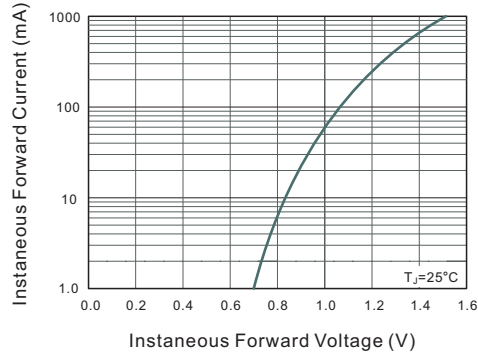
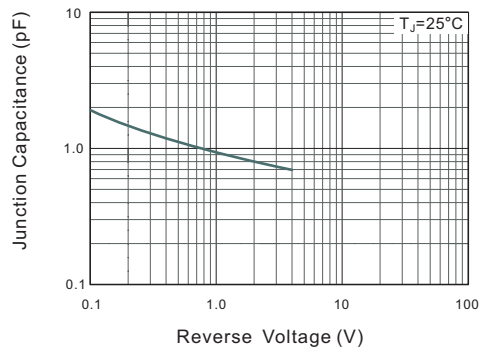


Fig.4 Typical Junction Capacitance

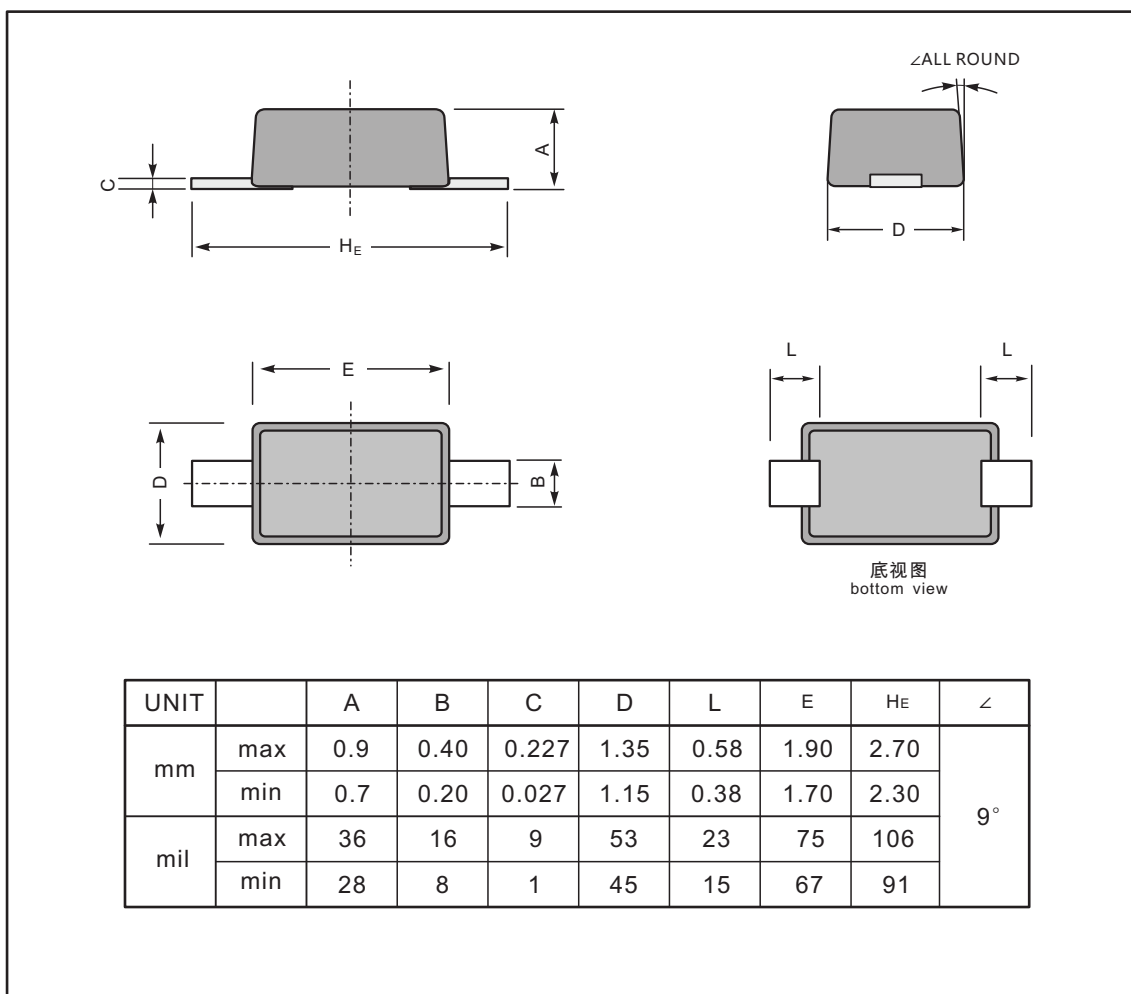




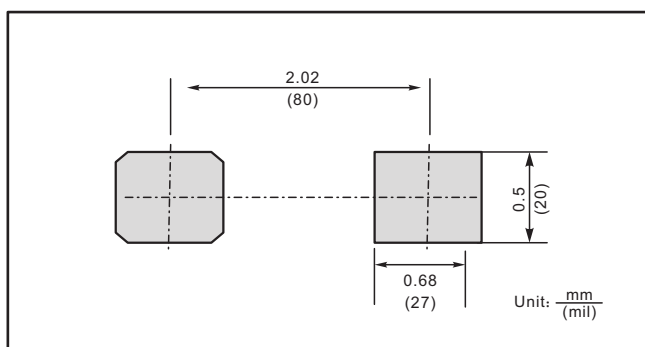
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323FLW



The recommended mounting pad size



Marking

Type number	Marking code
1N4148WF	T4

单击下面可查看定价，库存，交付和生命周期等信息

[>>JINGDAO\(晶导微\)](#)